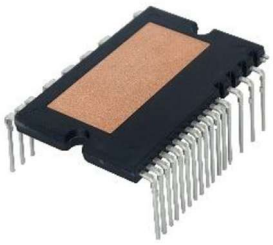
WSMG20T07MG1

IPM

Rev.01 - 22 Sep. 2026 **Product data sheet**

Features

- 650V 20A 3-Phase IGBT Inverter
- Low-Losses & Short-Circuit-Rated IGBTs
- Soft Reverse Recovery Diodes
- Built-In BootStrap Diodes
- Very Low Thermal Resistance with DBC Substrate
- Separate Open-Emitters from Low-Side IGBTs
- Under-Voltage Lock-Out for high side and low side
- Short-Circuit Protection
- Over Temperature Protection
- LVIC Temperature Output
- 3.3V and 5V Input Logic Compatible : Active High
- Fault Signaling : LVIC UVLO and Short-circuit Protection
- Isolation Rating of 1500 Vrms/1 min
- UL 1557 Certified(File E346397)



Typical Applications

- Air-conditioner, Washing machine etc.
- Motor Control - Industrial Motor (AC 200V Class)

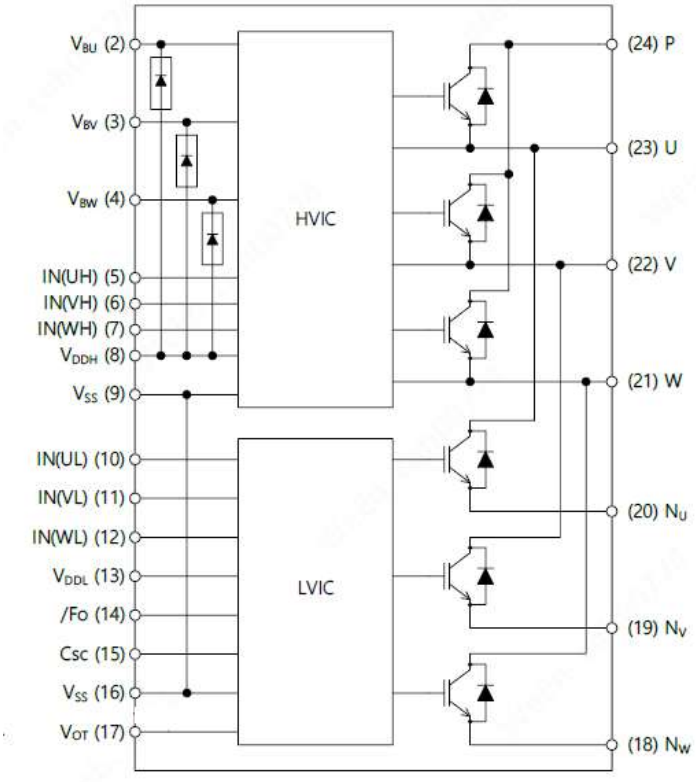


Figure 1. Internal Circuit

PIN DESCRIPTION

Pin Number	Pin Name	Pin Description
(1-1)	V_{SS}	Common Supply Ground, connected to HVIC
(1-2)	V_{DDH}	High-Side Bias Voltage for U Phase IC
2	V_{BU}	High-Side Bias Voltage for U Phase IGBT Driving
3	V_{BV}	High-Side Bias Voltage for V Phase IGBT Driving
4	V_{BW}	High-Side Bias Voltage for W Phase IGBT Driving
5	IN(UH)	Signal Input for High-Side U Phase
6	IN(VH)	Signal Input for High-Side V Phase
7	IN(WH)	Signal Input for High-Side W Phase
8	V_{DDH}	High-Side Bias Voltage for U Phase IC
9	V_{SS}	Common Supply Ground, connected to HVIC
10	IN(UL)	Signal Input for Low-Side U Phase
11	IN(VL)	Signal Input for Low-Side V Phase
12	IN(WL)	Signal Input for Low-Side W Phase
13	V_{DDL}	Low-Side Bias Voltage for IC and IGBTs Driving
14	/FO	Fault Output
15	Csc	Input for Current Protection
16	V_{SS}	Common Supply Ground, connected to LVIC
17	V_{OT}	Voltage Output for LVIC Temperature
18	N_W	Negative DC-Link Input for W Phase
19	N_V	Negative DC-Link Input for V Phase
20	N_U	Negative DC-Link Input for U Phase
21	W	Output for W Phase
22	V	Output for V Phase
23	U	Output for U Phase
24	P	Positive DC-Link Input
25	NC	Not Connected

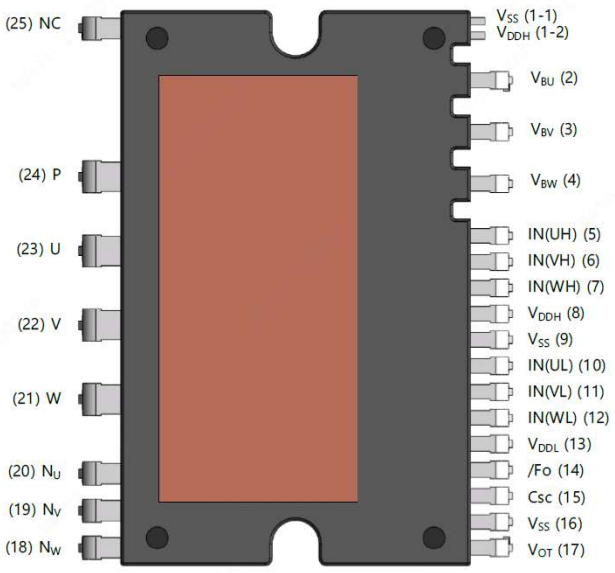


Figure 2. Pin Configuration

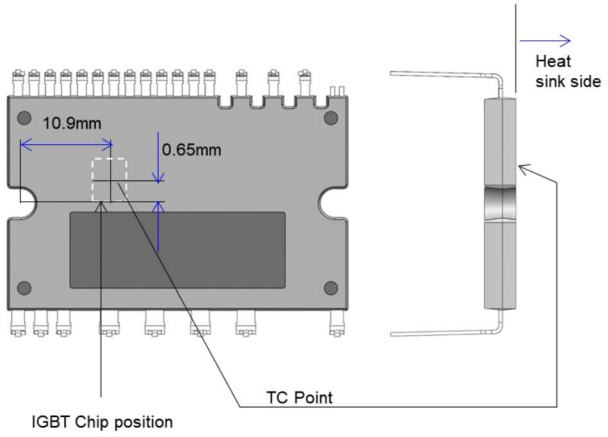


Figure 3. Tc Measurement Point

All information provided in this document is subject to legal disclaimers.
© WeEn Semiconductors Co., Ltd. 2026. All rights reserved

ABSOLUTE MAXIMUM RATINGS (Tj = 25°C unless otherwise noted)

Symbol	Rating	Conditions	Rating	Unit
INVERTER PART				
V_{PN}	Supply Voltage	Applied between P−N_U, N_V, N_W	450	V
$V_{PN(surge)}$	Supply Voltage (Surge)	Applied between P−N_U, N_V, N_W	550	V
V_{CES}	Collector-Emitter Voltage		650	V
I_C	Each IGBT Collector Current	T_C=25°C, T_j≤150°C	20	A
I_{CP}	Each IGBT Collector Current (Peak)	T_C=25°C, T_j≤150°C, Under 1ms Pulse Width (Note 1)	40	A
P_C	Collector Dissipation	T_C=25°C per One Chip (Note 1)	83	W
T_j	Operating Junction Temperature		−40~150	°C
CONTROL PART				
V_{DD}	Control Supply Voltage	Applied between V_{DDH}, V_{DDL}−V_{SS}	20	V
V_{BS}	High-Side Control Bias Voltage	Applied between V_{BU}−V_{SU}, V_{BV}−V_{SV}, V_{BW}−V_{SW}	20	V
V_{IN}	Input Signal Voltage	Applied between IN(UH), IN(VH), IN(WH), IN(UL), IN(VL), IN(WL) − V_{SS}	−0.5~V_{DD}+0.5	V
V_{FO}	Fault Output Supply Voltage	Applied between F_O−V_{SS}	−0.5~V_{DD}+0.5	V
I_{FO}	Fault Output Current	Sink Current at F_O pin	5	mA
V_{SC}	Current Sensing Input Voltage	Applied between C_{SC}−V_{SS}	−0.5~V_{DD}+0.5	V
T_j	Operating Junction Temperature		−40~150	°C
BOOSTSTRAP DIODE PART				
V_{RRM}	Maximum Repetitive Reverse Voltage		650	V
T_j	Operating Junction Temperature		−40~150	°C
TOTAL SYSTEM				
$V_{PN(PROT)}$	Self-Protection Supply Voltage Limit (Short-Circuit Protection Capability)	V_{DD}=V_{BS}=13.5~16.5V, T_j=150°C, Non-Repetitive, < 2 μs	400	V
T_C	Module Case Operation Temperature	See Figure 3	−40~125	°C
T_{stg}	Storage Temperature		−40~125	°C
V_{iso}	Isolation Voltage	60 Hz, Sinusoidal, AC 1 Minute, Connection Pins to Heat Sink Plate	1500	Vrms

Note 1: These values had been made an acquisition by the calculation considered to design factor.

THERMAL RESISTANCE

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-c)Q}$	Junction-to-Case Thermal Resistance (Note 2)	Inverter IGBT Part (per 1/6 module)	–	–	1.5	°C/W
$R_{th(j-c)F}$		Inverter FWDi Part (per 1/6 module)	–	–	2.4	°C/W

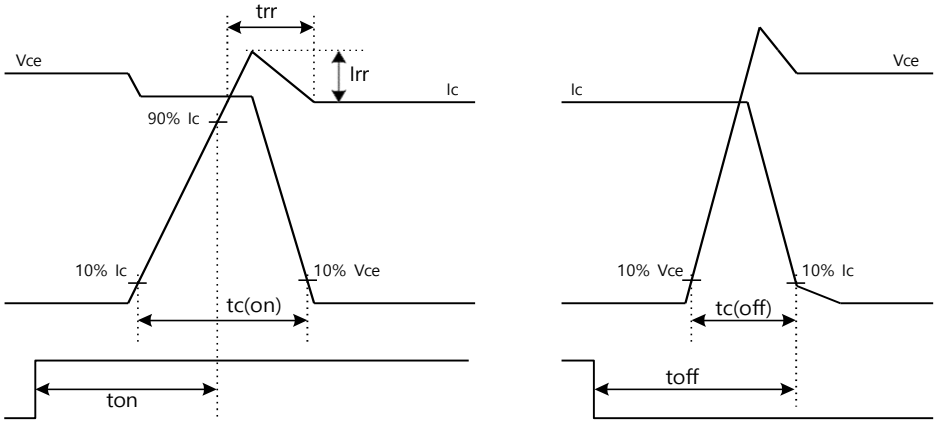
Note 2: For the measurement point of case temperature (Tc), please refer to Figure 3.

All information provided in this document is subject to legal disclaimers.
© WeEn Semiconductors Co., Ltd. 2026. All rights reserved

ELECTRICAL CHARACTERISTICS (Tj = 25°C unless otherwise specified.)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
INVERTER PART							
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V_{DD}=V_{BS}=15V V_{IN}=5V	I_C=20A, T_j=25°C	–	1.6	1.9	V
V_F	FWDi Forward Voltage	V_{IN}=0V	I_C=−20A, T_j=25°C	–	1.6	2.1	V
HS t_{on}	Switching Times	V_{PN}=300V, V_{DD}=15 V, I_C=20A T_j=25°C V_{IN}=0V↔5V, Inductive Load, See Figure 4 (Note 3)		–	1.5	–	µs
HS $t_{c(on)}$				–	0.2	–	µs
HS t_{off}				–	1.5	–	µs
HS $t_{c(off)}$				–	0.1	–	µs
HS t_{rr}				–	0.1	–	µs
LS t_{on}		V_{PN}=300V, V_{DD}=15 V, I_C=20A T_j=25°C V_{IN}=0V↔5V, Inductive Load, See Figure 4 (Note 3)		–	1.4	–	µs
LS $t_{c(on)}$				–	0.2	–	µs
LS t_{off}				–	1.4	–	µs
LS $t_{c(off)}$				–	0.1	–	µs
LS t_{rr}				–	0.1	–	µs
I_{CES}	Collector-Emitter Leakage Current	V_{CE} = V_{CES}		–	–	1	mA

Note 3: ton and toff include the propagation delay of the internal drive IC. tc(on) and tc(off) are the switching times of IGBT under the given gate-driving condition internally. For the detailed information, please see Figure 4.



(a) turn-on **(b) turn-off**

Figure 4. Switching Time Definition

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
CONTROL PART							
I_{QDDH}	Quiescent V_{DD} Supply Current	V_{DDH}=15V, $V_{IN(UH,VH,WH)}$=0V	V_{DDH}–V_{SS}	–	–	0.1	mA
I_{QDDL}		V_{DDL}=15V, $V_{IN(UL,VL,WL)}$=0V	V_{DDL}–V_{SS}	–	–	2.0	mA
I_{QBS}	Quiescent V_{BS} Supply Current	V_{DDH}=V_{DDL}=V_{BS}=15V, $V_{IN(UH,VH,WH)}$=0V	V_{BU}–V_{SU}, V_{BV}–V_{SV}, V_{BW}–V_{SW}	–	–	0.1	mA
V_{FOH}	Fault Output Voltage	V_{DDL}=15V, V_{sc}=0V, V_{FO} Circuit: 10kΩ to 5V Pull−up		4.90	–	–	V
V_{FOL}		V_{DDL}=15V, V_{sc}=1V, I_{FO}=1mA		–	–	0.95	V
$V_{SC(ref)}$	Short Circuit Trip Level (Note 4)	V_{DDL}=15V	C_{SC}–V_{SS}	0.455	0.48	0.505	V

All information provided in this document is subject to legal disclaimers.
© WeEn Semiconductors Co., Ltd. 2026. All rights reserved

ELECTRICAL CHARACTERISTICS (Tj = 25°C unless otherwise specified.) (continued)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
CONTROL PART							
U_{VDDD}	Supply Circuit Under-Voltage Protection	Detection Level		10.3	–	12.5	V
U_{VDDR}		Reset Level		10.8	–	13.0	V
U_{VBSD}		Detection Level		10.0	–	12.0	V
U_{VBSR}		Reset Level		10.5	–	12.5	V
I_{IN}	Input Current (Note 6)	V_{IN} = 5V		0.7	1.0	1.5	mA
$V_{IN(ON)}$	ON Threshold Voltage	Applied between $V_{IN(UH,VH,WH)}$–V_{SS}, $V_{IN(UL,VL,WL)}$–V_{SS}		–	–	2.6	V
$V_{IN(OFF)}$	OFF Threshold Voltage			0.8	–	–	V
OT_{trip}	Over temperature protection	V_{DDL}=15V Detect LVIC temperature	Trip level	130	140	150	°C
OT_{hys}			Hysteresis of trip-reset		10		°C
V_{OT}	Voltage Output for LVIC Temperature Sensing Unit	V_{DDL}=15V, T_{LVIC}=25°C See Figure 4 and 5 (Note 5)		0.88	1.13	1.39	V
t_{FOD}	Fault-Out Pulse Width			20	–	–	us

Note 4: Short-circuit current protection functions only at the low-sides because the sense current is divided from main current at low-side IGBTs. Inserting the shunt resistor for monitoring the phase current at NU, NV, NW terminal, the trip level of the short-circuit current is changed.

Note 5: T_{LVIC} is LVIC temperature and V_{OT} is only for sensing the temperature of LVIC and cannot shut down IGBTs automatically. The relationship between V_{OT} voltage output and LVIC temperature is described in Figure 5. It is recommended to add a ceramic capacitor of 10 nF or more between V_{OT} and V_{SS} to make the V_{OT} more stable. Refer to the application note for this product about usage of V_{OT}.

Note 6: RC coupling at each input might change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board. The input signal section integrates 5 kΩ (typ.) pull-down resistor. Therefore, when using an external filtering resistor, please pay attention to the signal voltage drop at the input terminal.

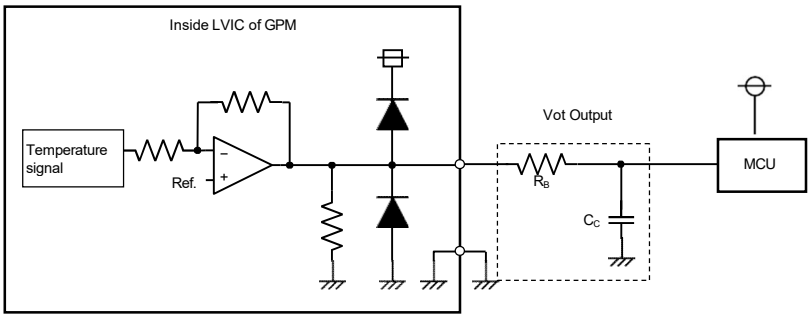


Figure 5. Internal Block Diagram and Interface Circuit of V_{OT}

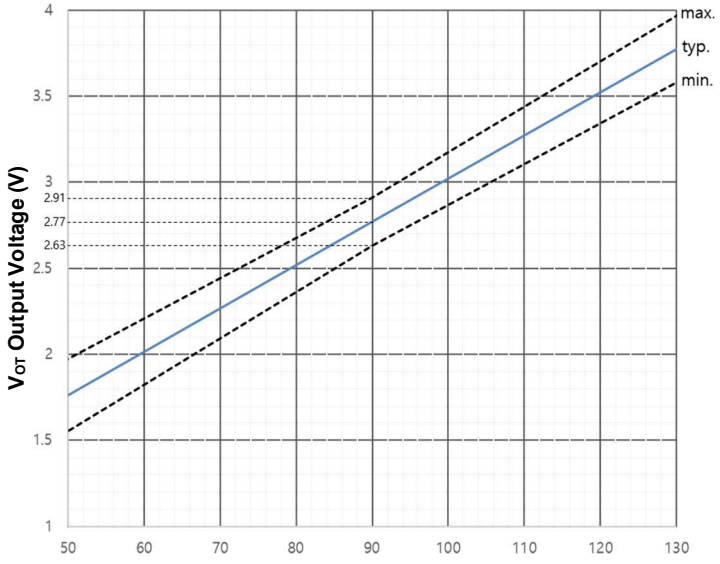


Figure 6. Temperature Profile of V_{OT}

All information provided in this document is subject to legal disclaimers.
© WeEn Semiconductors Co., Ltd. 2026. All rights reserved

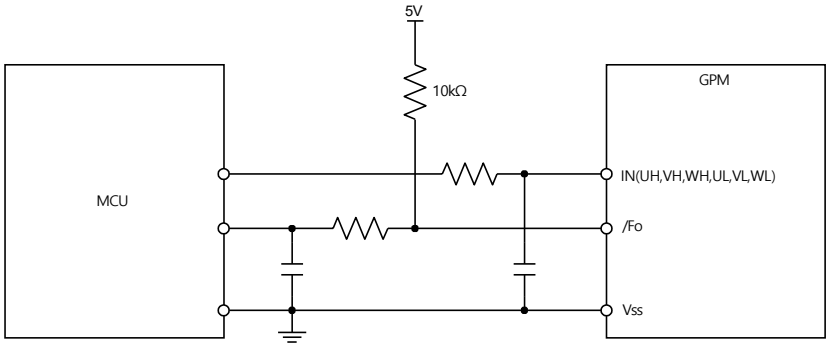


Figure 7. Recommended MCU I/O Interface Circuit

ELECTRICAL CHARACTERISTICS (Tj = 25°C unless otherwise specified.) (continued)

BOOTSTRAP DIODE/RESISTOR PART

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_F	Forward Voltage	I_F=0.01A, T_j=25°C	See Figure 8	–	1.6	–	V

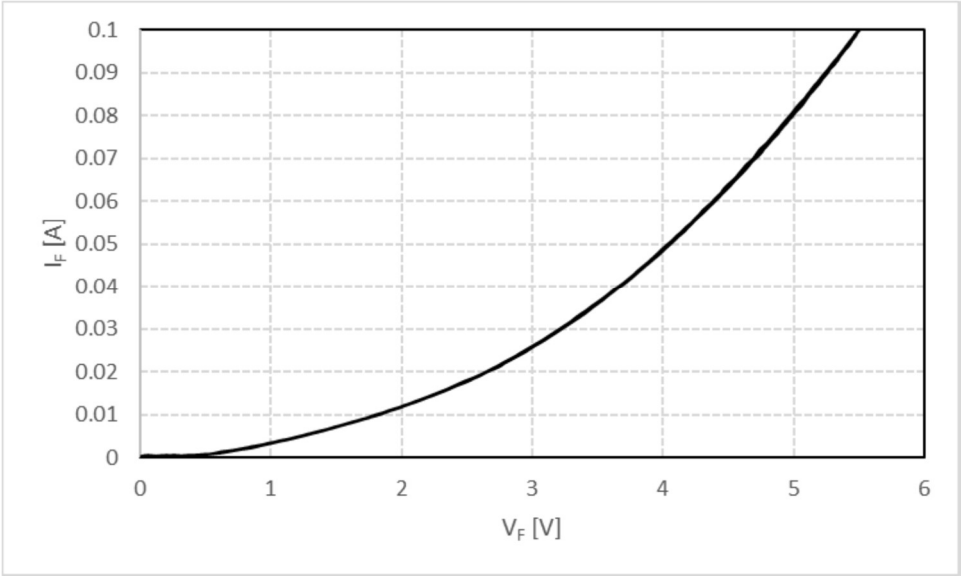


Figure 8. Characteristics of Bootstrap Diode

RECOMMENDED OPERATING RANGES

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PN}	Supply Voltage	Applied between P−N_U, N_V, N_W	–	300	400	V
V_{DD}	Control Supply Voltage	Applied between V_{DDH}−V_{SS}, V_{DDL}−V_{SS}	13.5	15.0	16.5	V
V_{BS}	High-Side Control Bias Voltage	Applied between V_{BU}−V_{SU}, V_{BV}−V_{SV}, V_{BW}−V_{SW}	13.0	15.0	18.5	V
dV_{DD}/dt, dV_{BS}/dt	Control Supply Variation		−1	–	+1	V/µs
t_{dead}	Blanking Time for Preventing Arm − Short	For Each Input Signal	1.0	–	–	µs
f_{PWM}	PWM Input Signal	−40°C≤T_C≤125°C, −40°C≤T_j≤150°C	–	–	20	kHz
PWIN(ON)	Minimum Input Pulse Width	(Note 7)	0.7	–	–	µs
PWIN(OFF)			0.7	–	–	
T_j	Junction Temperature		−40	–	+150	°C

Note 7: This product might not make output response if input pulse width is less than the recommended value.

All information provided in this document is subject to legal disclaimers.
© WeEn Semiconductors Co., Ltd. 2026. All rights reserved

PACKAGE MARKING AND ORDERING INFORMATION

Device	Device Marking	Package	Shipping
WSMG20T07MG1	WSMG20T07MG1	DIP24	480 ea/box

MECHANICAL CHARACTERISTICS AND RATINGS

Parameter	Conditions	Min	Typ	Max	Unit
Device Flatness	See Figure 9	−50	–	120	μm
Mounting Torque	Mounting Screw: M3	0.59	0.69	0.78	N·m
Terminal Pulling Strength	Control terminal : Load 5N Power terminal : Load 10N	10	–	–	s
Terminal Bending Strength	Control terminal : Load 5N Power terminal : Load 10N 90 degree Bend	2	–	–	times
Weight		–	9.6	–	g

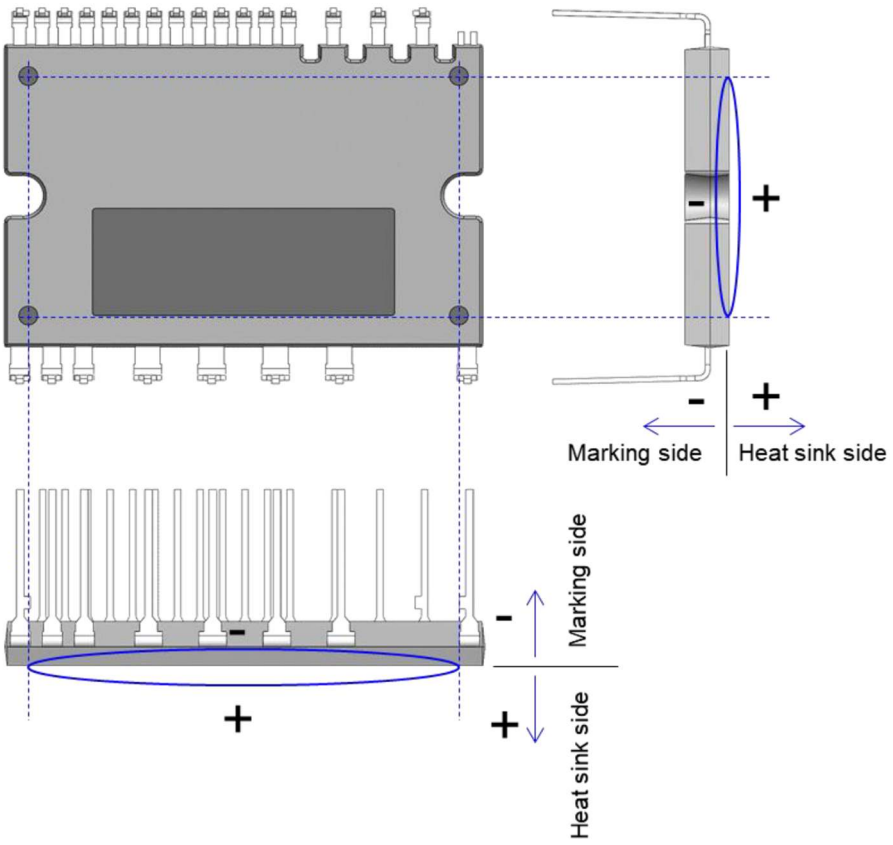
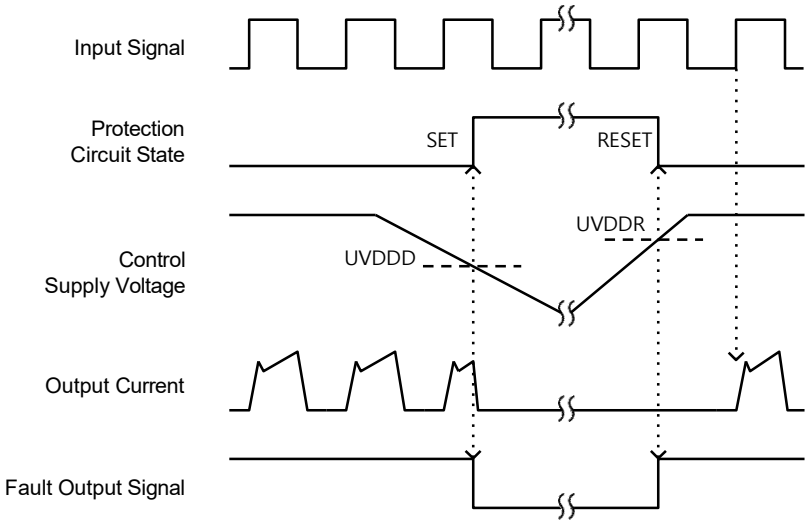


Figure 9. Flatness Measurement Position

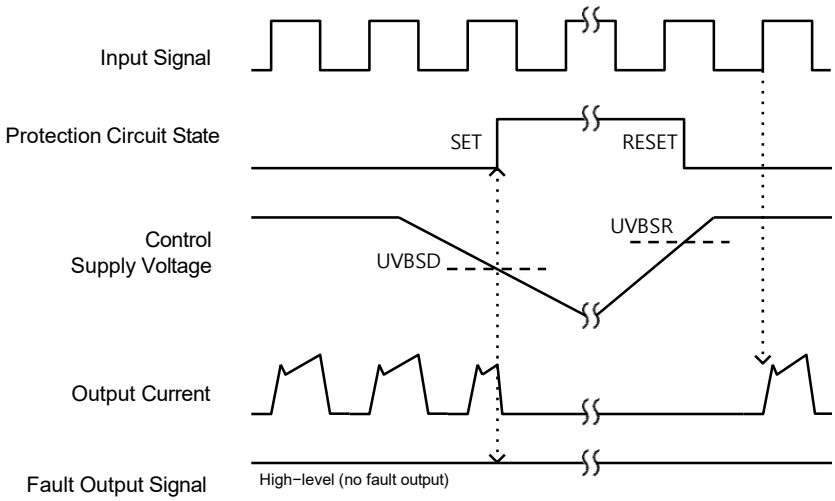
All information provided in this document is subject to legal disclaimers.
© WeEn Semiconductors Co., Ltd. 2026. All rights reserved

TIME CHARTS OF GPMs PROTECTIVE FUNCTION



1: Normal operation: IGBT ON and carrying current.
2: Under-voltage detection (UVDDD).
3: IGBT OFF in spite of control input condition.
4: Fault output operation starts with a fixed pulse width (min. 20us).
5: Under-voltage reset (UVDDR).
6: Normal operation: IGBT ON and carrying current by triggering next signal from LOW to HIGH.

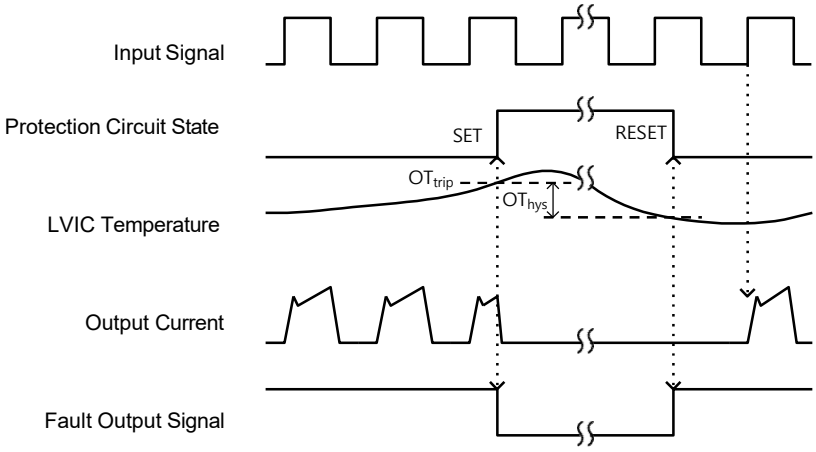
Figure 10. Under-voltage Protection (Low-side)



1: Normal operation: IGBT ON and carrying current.
2: Under-voltage detection (UVBSD).
3: IGBT OFF in spite of control input condition, but there is no fault output signal.
4: Under-voltage reset (UVBSR).
5: Normal operation: IGBT ON and carrying current by triggering next signal from LOW to HIGH.

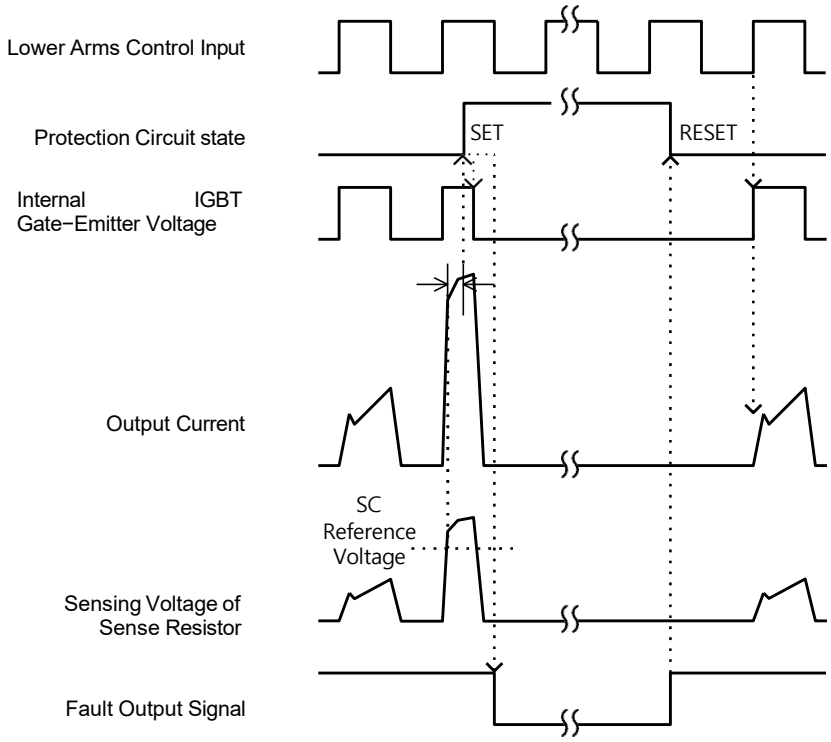
Figure 11. Under-voltage Protection (High-side)

All information provided in this document is subject to legal disclaimers.
© WeEn Semiconductors Co., Ltd. 2026. All rights reserved



1: Normal operation: IGBT ON and carrying current.
2: LVIC temperature exceeds OT trip level (OT_{trip}).
3: All low-side IGBTs OFF in spite of control input condition.
4: Fault output operation starts with a fixed pulse width (min. 20us).
5: LVIC temperature drop to OT reset level.
6: Normal operation: IGBT ON and carrying current by triggering next signal from LOW to HIGH.

Figure 12. Over-temperature Protection



1: Normal operation: IGBT ON and carrying current.
2: Short-circuit current detection (SC trigger).
3: All low-side IGBTs gates are hard interrupted.
4: All low-side IGBTs turn OFF.
5: Fault output operation starts with a fixed pulse width (min. 20us).
6: Input HIGH − IGBT ON state, but during the active period of fault output, the IGBT doesn't turn ON.
7: Fault output operation finishes, but IGBT doesn't turn on until triggering the next signal from LOW to HIGH.
8: Normal operation: IGBT ON and carrying current.

Figure 13. Short-circuit Current Protection (Low-side Operation Only)

All information provided in this document is subject to legal disclaimers.
© WeEn Semiconductors Co., Ltd. 2026. All rights reserved

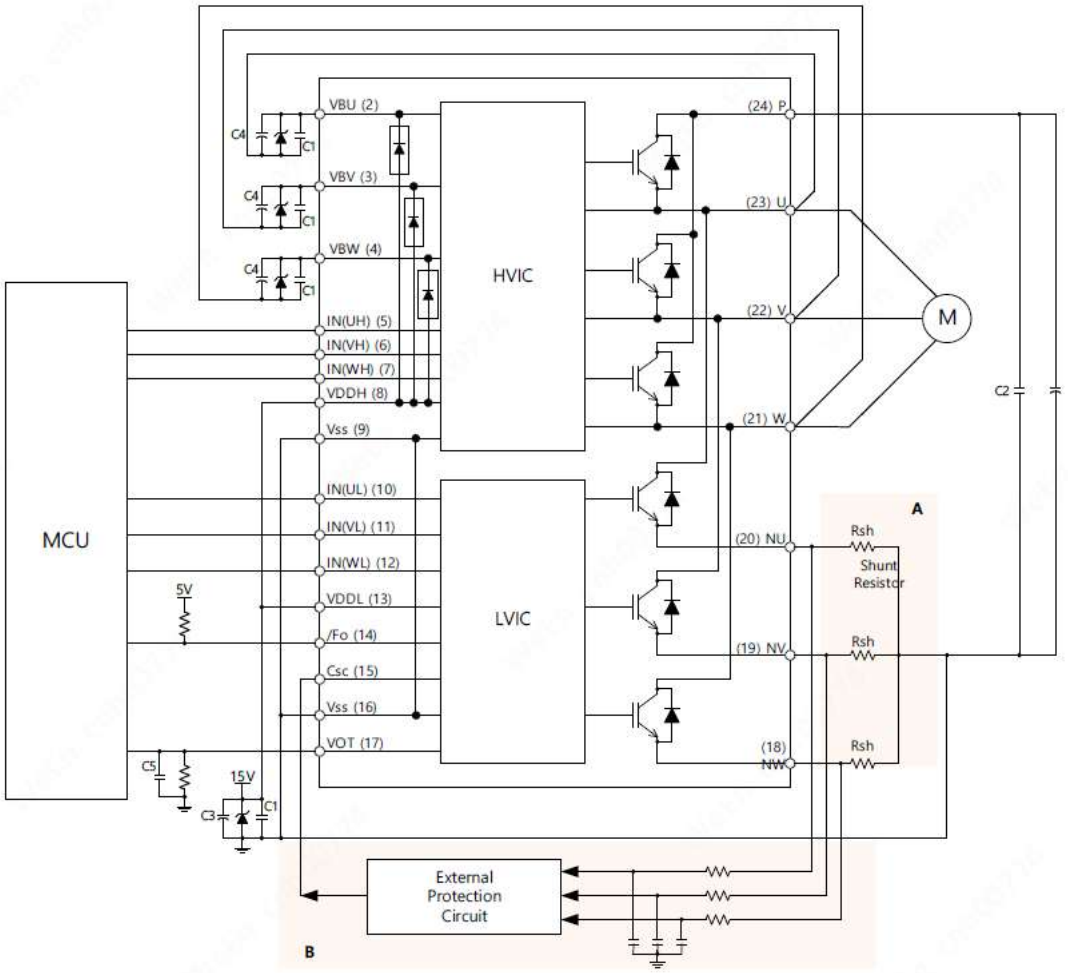
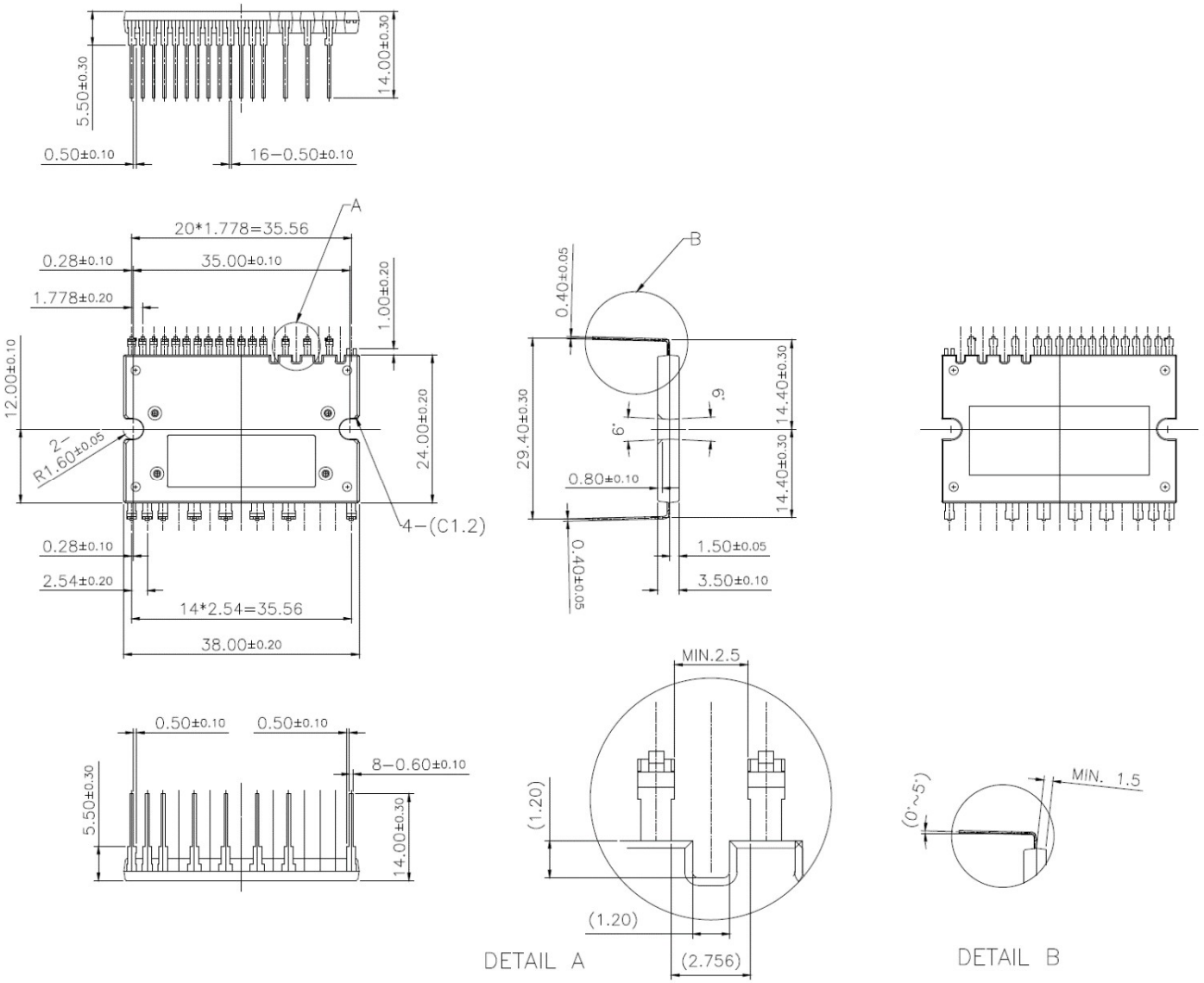


Figure 14. Typical Application Circuit

1. To avoid malfunction, the wiring of each input should be as short as possible (less than 2−3 cm).
2. Fault output is an open-drain type. This signal line should be pulled up to the positive side of the MCU or control power supply with a resistor that makes I_{FO} up to 1 mA. Please refer to Figure 6.
3. Input signal is active-HIGH type. There is a 5 kΩ resistor inside the IC to pull-down each input signal line to GND. RC coupling circuits should be adopted for the prevention of input signal oscillation. RC time constant should be selected in the range 50~150 ns (recommended R = 100Ω, C = 1 nF). Please refer to Figure 6.
4. Each wiring pattern inductance of point A should be minimized (recommend less than 10 nH). Use the shunt resistor Rsh of surface mounted (SMD) type to reduce wiring inductance.
5. To insert the shunt resistor to measure each phase current at N_U, N_V, N_W terminal, it makes to change the trip level I_{SC} about the short-circuit current.
6. To prevent errors in the protection function, the wiring of point B should be as short as possible.
7. For stable protection function, use the sense resistor Rsh with resistance variation within 1% and low inductance value.
8. In the short-circuit protection circuit, select the RC time constant of protection circuit in the range 2.0~2.5 μs.
9. Each capacitor C1 should be mounted as close to the pins of the GPM product as possible.
10. To prevent surge destruction, the wiring between the smoothing capacitor C2 and the P & GND pins should be as short as possible. The use of a high-frequency non-inductive capacitor of around 0.1~0.22 μF between the P & GND pins is recommended.
11. Relays are used in most systems of electrical equipment in industrial application. In these cases, there should be sufficient distance between the MCU and the relays.
12. The Zener diode or transient voltage suppressor should be adopted for the protection of ICs from the surge destruction between each pair of control supply terminals (recommended Zener diode is 22V/1W, which has the lower Zener impedance characteristic than about 15 Ω).
13. C3 of around seven times larger than bootstrap capacitor C4 is recommended.
14. Please choose the electrolytic capacitor with good temperature characteristics in C4. Choose 0.1~0.2μF R-category ceramic capacitors with good temperature and frequency characteristics in C1.
15. For stable analog voltage output for LVIC temperature, please use ceramic capacitor for C5.

All information provided in this document is subject to legal disclaimers.
© WeEn Semiconductors Co., Ltd. 2026. All rights reserved

PACKAGE DIMENSIONS



All information provided in this document is subject to legal disclaimers.
© WeEn Semiconductors Co., Ltd. 2026. All rights reserved

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ween-semi.com.

Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. WeEn Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local WeEn Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between WeEn Semiconductors and its customer, unless WeEn Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the WeEn Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, WeEn Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. WeEn Semiconductors takes no responsibility for the content in this document if provided by an information source outside of WeEn Semiconductors.

In no event shall WeEn Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, WeEn Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of WeEn Semiconductors.

Right to make changes — WeEn Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — WeEn Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an WeEn Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. WeEn Semiconductors and its suppliers accept no liability for inclusion and/or use of WeEn Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. WeEn Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using WeEn Semiconductors products, and WeEn Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the WeEn Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

WeEn Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using WeEn Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). WeEn does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Non-automotive qualified products — Unless this data sheet expressly states that this specific WeEn Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. WeEn Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without WeEn Semiconductors' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond WeEn Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies WeEn Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond WeEn Semiconductors' standard warranty and WeEn Semiconductors' product specifications.

All information provided in this document is subject to legal disclaimers.
© WeEn Semiconductors Co., Ltd. 2026. All rights reserved

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

All information provided in this document is subject to legal disclaimers.
© WeEn Semiconductors Co., Ltd. 2026. All rights reserved

14. Contents

1. General description 1
2. Features and benefit 1
3. Applications 1
4. Quick reference data 1
5. Pinning information 2
6. Ordering information 2
7. Marking 2
8. Limiting values 3
9. Thermal characteristics 4
10. Characteristics 5
11. Switching Characteristics 6
12. Package outline 11
13. Legal information 12
14. Contents 14

© WeEn Semiconductors Co., Ltd. 2026. All rights reserved

For more information, please visit: http://www.ween-semi.com
For sales o ice addresses, please send an email to: salesaddresses@ween-semi.com
Date of release: 20 September 2026